

TOSHIBA HIGH EFFICIENCY DIODE STACK (HED) SILICON EPITAXIAL TYPE

10DL2CZ47A, 10FL2CZ47A, 10GL2CZ47A

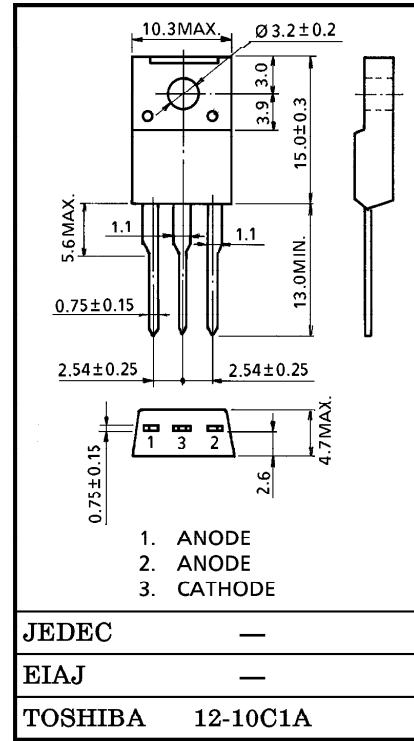
SWITCHING TYPE POWER SUPPLY APPLICATION
CONVERTER & CHOPPER APPLICATION

Unit in mm

- Repetitive Peak Reverse Voltage : $V_{RRM}=200, 300, 400V$
- Average Output Rectified Current : $I_O=10A$
- Ultra Fast Reverse-Recovery Time : $t_{rr}=35ns$ (Max.)
- Low Switching Losses and Output Noise.

MAXIMUM RATINGS

CHARACTERISTIC		SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	10DL2CZ47A	V_{RRM}	200	V
	10FL2CZ47A		300	
	10GL2CZ47A		400	
Average Output Rectified Current		I_O	10	A
Peak One Cycle Surge Forward Current (Sine Wave)		I_{FSM}	50 (50Hz)	A
			55 (60Hz)	
Junction Temperature		T_j	-40~150	°C
Storage Temperature Range		T_{stg}	-40~150	°C
Screw Torque		—	0.6	N·m



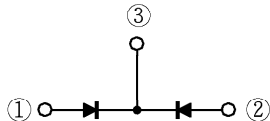
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Weight : 2.0g

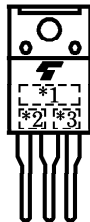
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage (Note 1)	10DL2CZ47A	V_{FM}	$I_{FM}=5A$	—	—	0.98	V
	10FL2CZ47A			—	—	1.3	
	10GL2CZ47A			—	—	1.8	
Repetitive Peak Reverse Current (Note 1)	10DL2CZ47A	I_{RRM}	$V_{RRM}=\text{Rated}$	—	—	10	μA
	10FL2CZ47A			—	—	10	
	10GL2CZ47A			—	—	50	
Reverse Recovery Time (Note 1)		t_{rr}	$I_F=2A, di/dt=-20A/\mu s$	—	—	35	ns
Forward Recovery Time (Note 1)		t_{fr}	$I_F=1A$	—	—	100	ns
Thermal Resistance		$R_{th(j-c)}$	DC Total, Junction to Case	—	—	3.6	°C/W

(Note 1) A value of one cell.

POLARITY



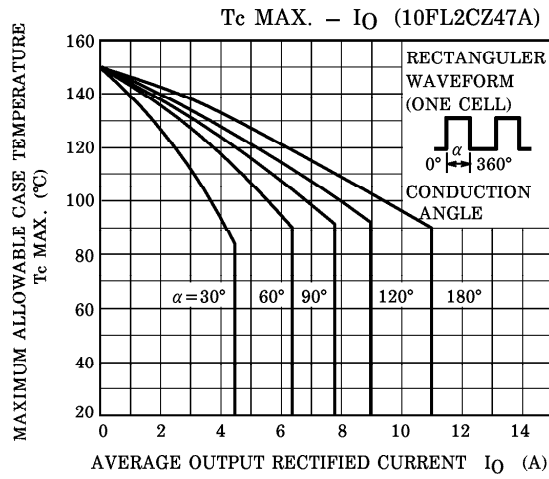
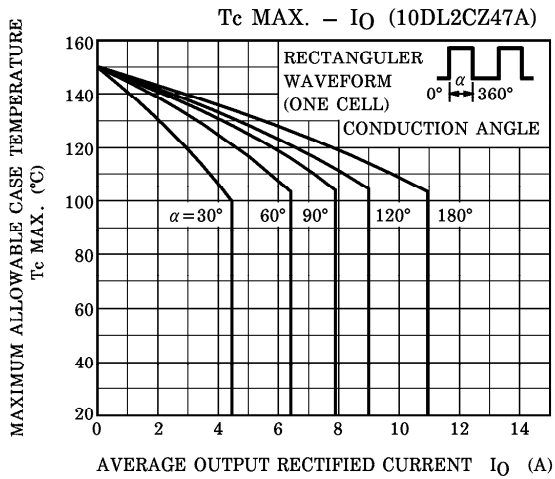
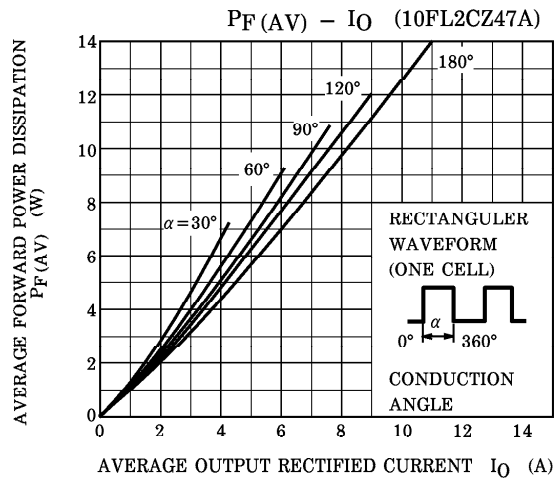
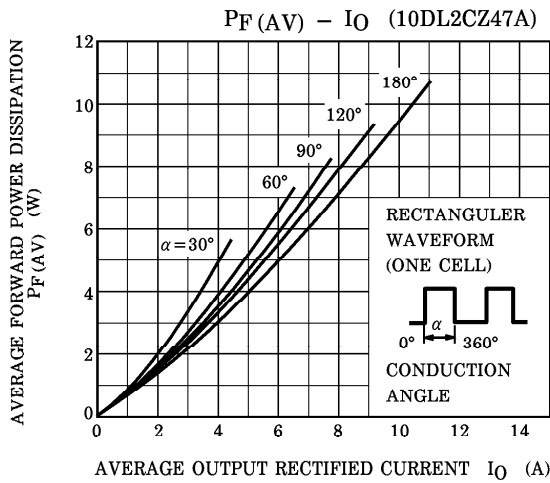
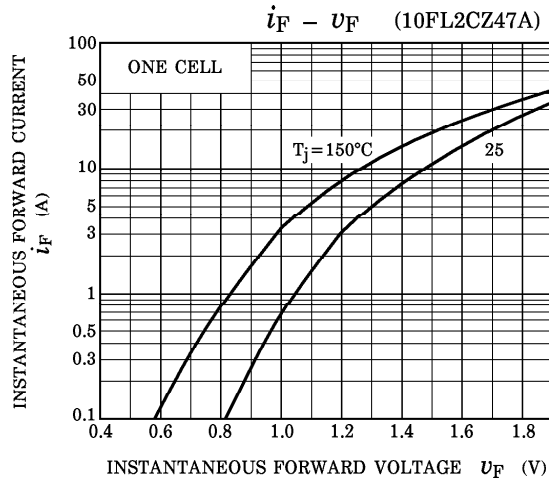
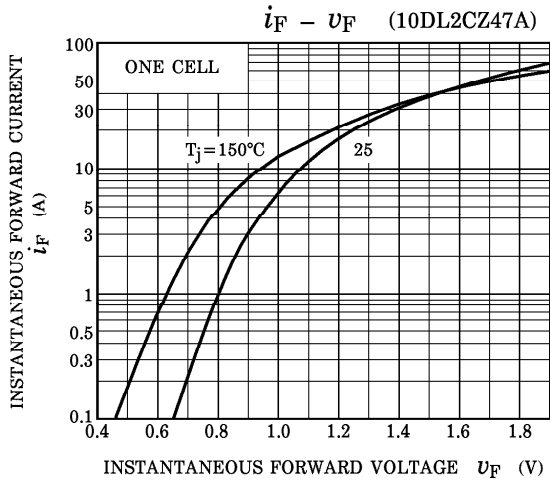
MARKING



*1	MARK	10DL2CZ	TYPE	10DL2CZ47A
		10FL2CZ		10FL2CZ47A
		10GL2CZ		10GL2CZ47A
*2	A			
*3	Lot Number			
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